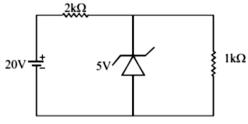
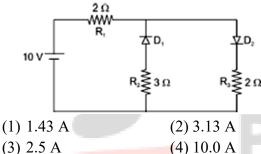


PHYSICS

21. Find current through Zener diode



- (1) 5 mA
- (2) 7.5 mA
- (3) 2.5 mA
- (4) 12.5 mA
- 22. The given circuit has two ideal diodes connected as shown in the figure below. The current flowing through the resistance R will be



23. The truth table shown below is for which of the following gates?

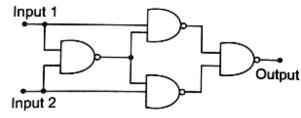
ates:			
	A	В	Y
	1	1	0
	1	0	0
	0	1	0
	0	0	1

- (1) AND
- (2) NAND
- (3) XOR
- (4) NOR
- 24. How many NAND gates are used to form AND gate?
 - (1) 3

(2) 2

(3) 1

- (4)4
- 25. For the following combination of gates select the correct statement



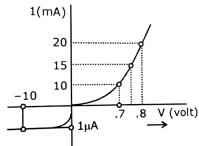
- (1) The output is I when both the inputs are 1
- (2) The output is 0 when both the inputs are 0

- (3) The output is 0 when the two inputs differ
- (4) The output is I when the two inputs differ
- 26. **Statement-I:** By doping silicon semiconductor with pentavalent material, the electrons density increases

Statement-II: Then-type semiconductor has net negative charge

In the light of the above statements, choose the most appropriate answer from the options given below

- (1) Statement-I is true but Statement-II is false.
- (2) Statement-I is false but Statement-II is true
- (3) Both Statement-I and Statement-II are true.
- (4) Both Statement-I and Statement-II are .false.
- 27. In a semiconductor the number density of intrinsic charge carries at 27° C is 1.5×10^{16} m⁻³. If the semiconductor is doped with impurity atom. the hole density increases to 4.5×10^{22} m⁻³. The electron density in the doped semiconductor is $\times 10^{9}$
 - $(1) 5 \times 10^9 \text{ m}^{-3}$
- $(2) 6 \times 10^9 \,\mathrm{m}^{-3}$
- (3) $7 \times 10^9 \,\mathrm{m}^{-3}$
- (4) $8 \times 10^9 \text{ m}^{-3}$
- 28. Consider a situation in which reverse biased current of a particular P-N junction increases when it is exposed to Light of Wavelength <621 nm. During this process enhancement in carrier concentration takes place due to generation of hole-electron pairs. The value of band gap is nearly
 - (1) 2 eV (2) 4 eV
- (3) 1 e V (4) 0.5 eV
- 29. The V-I characteristic of a diode is shown in the figure The ratio of forward to reverse bias resistance is



2



(1) 10

 $(2)\ 10^{-6}$

 $(3) 10^6$

- (4) 100
- 30. A ray of light falls on the surface of a spherical glass paper weight making an angle α with the normal and is refracted in the medium at an angle β . The angle of deviation of the emergent ray from the direction of the incident ray is
 - $(1)(\alpha \beta)$
- $(2) 2(\alpha \beta)$
- $(3) \ \frac{(\alpha \beta)}{2}$
- $(4)(\alpha + \beta)$

